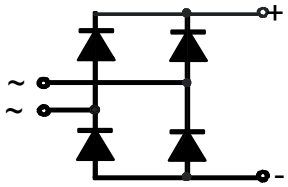
Single Phase Rectifier Bridge

PSB 25MB
PSB 25MBN

I_{dAVM} = 21 A
V_{RRM} = 200 V to 1000 V

Preliminary Data Sheet

V_{RSM} V	V_{RRM} V	Type Number	
		Gold-plated terminals	Nickel-plated terminals
200	200	PSB 25MB/02	PSB 25MBN/02
400	400	PSB 25MB/04	PSB 25MBN/04
600	600	PSB 25MB/06	PSB 25MBN/06
800	800	PSB 25MB/08	PSB 25MBN/08
1000	1000	PSB 25MB/10	PSB 25MBN/10



Symbol	Test Conditions			Maximum Ratings	
I_{dAVM}	T_c = 63°C per module			21	A
I_{FSM}	T_{vj} = 45°C, V_R = 0 V	t = 10 ms	50 Hz, sine	230	A
	T_{vj} = T_{vjm}, V_R = 0 V	t = 10 ms	50 Hz, sine	220	A
$\int i^2dt$	T_{vj} = 45°C, V_R = 0 V	t = 10 ms	50 Hz, sine	725	A^2s
	T_{vj} = T_{vjm}, V_R = 0 V	t = 10 ms	50 Hz, sine	800	A^2s
T_{vj}				-40 ... +150	°C
T_{vjm}				150	°C
T_{stg}				-40 ... +150	°C
V_{isol}	50/60 Hz, RMS	t = 1 min		2500	V~
	I_{isol} ≤ 1mA	t = 1 s		3000	V~
M_d	Mounting torque	(M5)		2±10%	Nm
		(10-32 UNF)		18±10%	lb in
Weight	typ.			20	g

Symbol	Test Conditions			Characteristic Value	
I_R	V_R = V_{RRM}	T_{vj} = 25°C	≤	0.3	mA
	V_R = V_{RRM}	T_{vj} = T_{vjm}	≤	2.0	mA
V_F	I_F = 150 A	T_{vj} = 25°C	≤	2.2	V
V_{TO}	For power-loss calculations only			0.85	V
r_T	T_{vj} = T_{vjm}			12	mΩ
$R_{th(j-c)}$	per diode; DC current			8.2	K/W
	per module			2.05	K/W
$R_{th(j-s)}$	per diode; DC current			9.4	K/W
	per module			2.35	K/W
d_S	Creeping distance on surface			12.7	mm
d_A	Creeping distance on air			9.4	mm
a	Maximum allowable acceleration			50	m/s^2

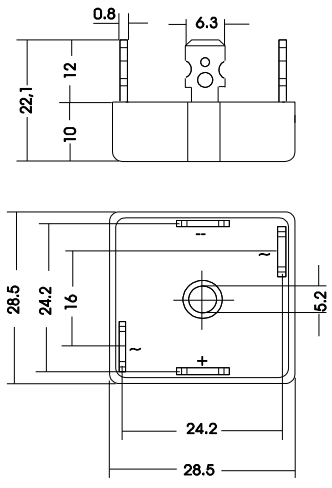
Data according to IEC 60747 refers to a single diode unless otherwise stated

Features
- ¼" gold- or nickel-plated FASTON terminals
- Isolation voltage 3000 V~
- Mesa glass-passivated chips
- Blocking voltage up to 1000 V
- Low forward voltage drop
- UL registered E 148688

Applications
- Supplies for DC power equipment
- Input rectifiers for PWM inverters
- Battery DC power supplies

Advantages
- Easy to mount with one screw
- Space and weight savings

Package style and outline



Dimensions in mm (1mm = 0.0394")